Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# RFM01U7P

## VHF- and UHF-band Amplifier Applications

(Note)The TOSHIBA products listed in this document are intended for high frequency Power Amplifier of telecommunications equipment. These TOSHIBA products are neither intended nor warranted for any other use. Do not use these TOSHIBA products listed in this document except for high frequency Power Amplifier of telecommunications equipment.

• Output power: Po = 1.2 W (typ.)

• Gain: GP = 10.8 dB (typ.)

• Drain efficiency:  $\eta_D = 65\%$  (typ.)

## Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	20	V
Gate-source voltage	$V_{GSS}$	10	V
Drain current	ΙD	1	Α
Power dissipation	P <sub>D</sub> (Note 1)	3	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-45 to 150	°C

1. GATE
2. SOURCE
3. DRAIN

DEDEC

JEITA

4.6MAX.

1.6MAX.

0.4±0.05

0.4±0.05

1.5±0.1

1.5±0.1

1.5±0.1

1.5±0.1

1.5±0.1

1.5±0.1

1.5±0.1

1.5±0.1

1.5±0.1

1.5±0.1

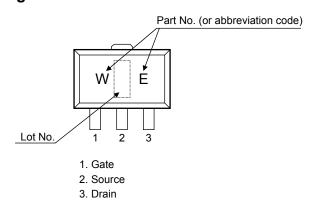
Weight: 0.05 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in

temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Tc = 25°C (When mounted on a 1.6 mm glass epoxy PCB)

## Marking



**Caution:** This device is sensitive to electrostatic discharge.

Please make enough tool and equipment earthed when you handle.

Start of commercial production 2008-11

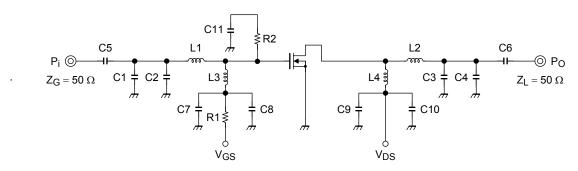
## **Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain cut-off current	I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	10	μА
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = 10 V	_	_	5	μА
Threshold voltage	$V_{th}$	$V_{DS} = 7.2 \text{ V}, I_D = 0.5 \text{ mA}$	0.6	1.1	1.6	V
Output power	Po	$\begin{split} &V_{DS}=7.2 \text{ V,} \\ &I_{idle}=100 \text{ mA (V}_{GS}=\text{adjust),} \\ &f=520 \text{ MHz, P}_i=100 \text{ mW,} \\ &Z_G=Z_L=50 \Omega \end{split}$	1.0	1.2	_	W
Drain efficiency	η <sub>D</sub>		55	65	_	%
Power gain	G <sub>P</sub>		10.0	10.8	_	dB
Load mismatch	_	$\begin{split} V_{DS} &= 12.5 \text{ V}, \\ P_O &= 1.2 \text{ W(P}_i = \text{adjust)}, \\ I_{idle} &= 100 \text{ mA (V}_{GS} = \text{adjust)}, \\ f &= 520 \text{ MHz}, \\ \text{VSWR LOAD 20:1 all phase} \end{split}$	No degradation			

Note 2: These characteristic values are measured using measurement tools specified by Toshiba.

## **Output Power Test Fixture**

(Test Condition: f = 520 MHz,  $V_{DS} = 7.2 \text{ V}$ ,  $I_{idle} = 100 \text{ mA}$ ,  $P_i = 100 \text{ mW}$ )



C1: 15 pF C2: 10 pF C3: 9 pF

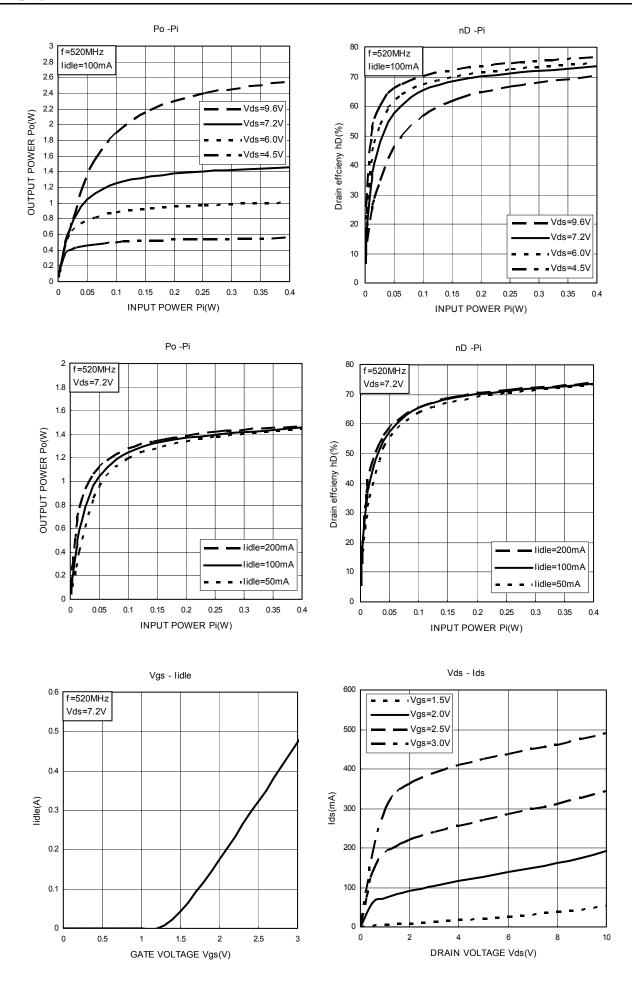
C4: 6 pF C5: 2200 pF C6: 2200 pF

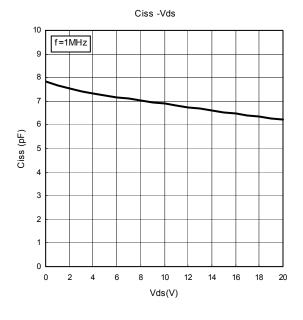
C7: 10 μF C8: 10000 pF C9: 10 μF

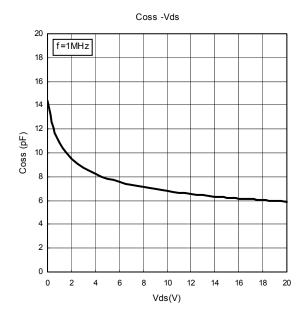
C10: 10000 pF C11: 2200 pF L1:  $\phi$ 0.8 mm enamel wire, 2.2ID, 1T R1: 1.5 k $\Omega$  L2:  $\phi$ 0.8 mm enamel wire, 2.2ID, 1T R2: 51  $\Omega$ 

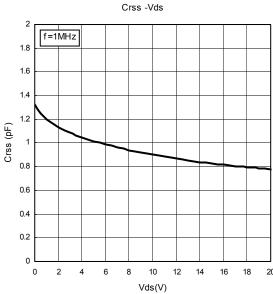
L3: φ0.8 mm enamel wire, 5.5ID, 4T L4: φ0.8 mm enamel wire, 5.5ID, 8T

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Note 3: These are only typical curves and devices are not necessarily guaranteed at these curves.

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